

Workshop on fast Cherenkov detectors

Giessen , 11-13 May 2009

Microelectronics  
for  
Silicon-PM readout

Christophe de La Taille , LAL Orsay, France

Presented by Joël Pouthas , IPN Orsay

# Omega

Orsay Micro-Electronics

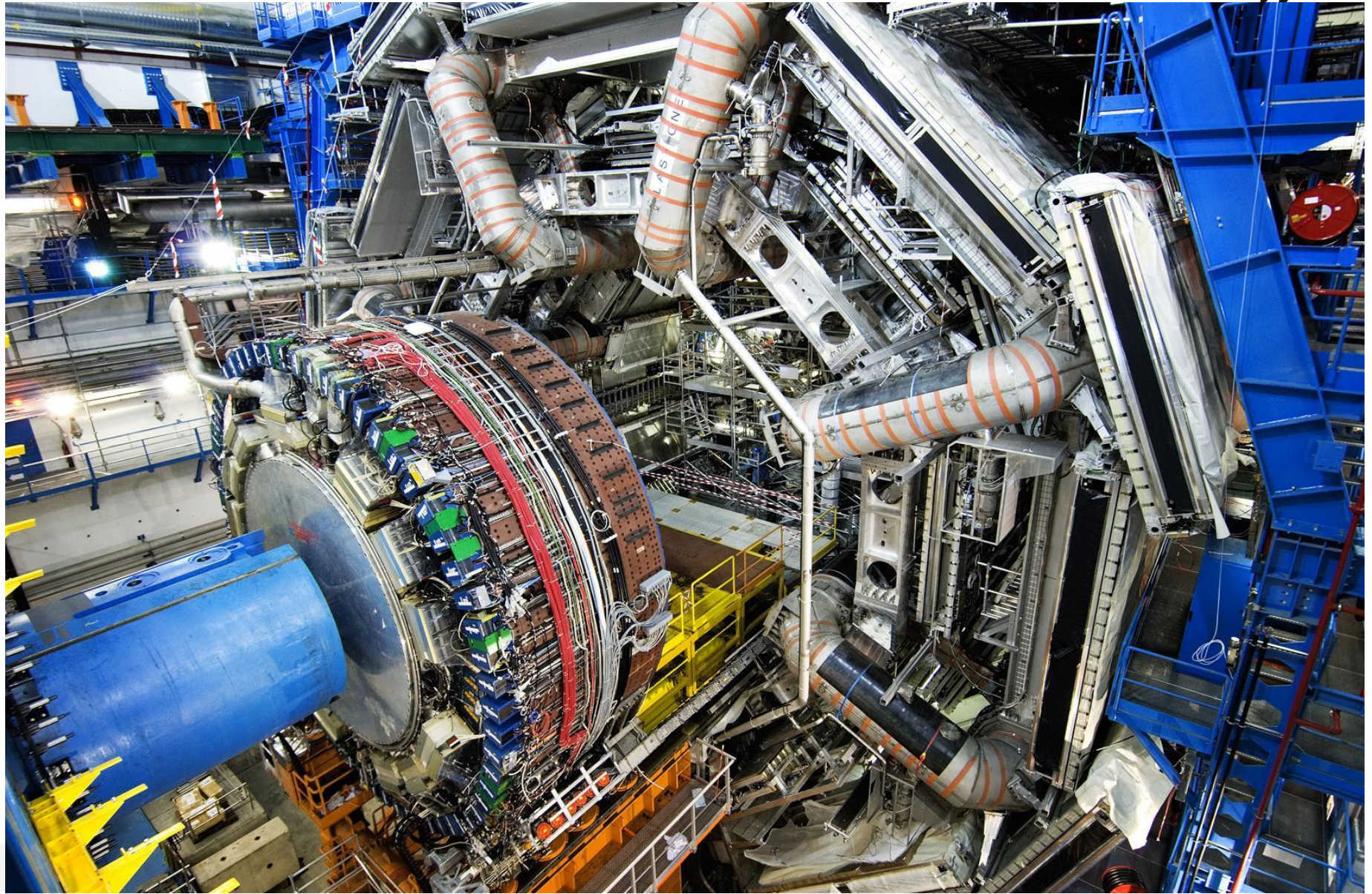
Groups Associated

P. Barrillon, S. Blin, S. Callier, S. Conforti, F.  
Dulucq, J. Fleury, C. de La Taille, G. Martin-  
Chassard, L. Raux, N. Seguin-Moreau

+ Wei Wei from IHEP Beijing

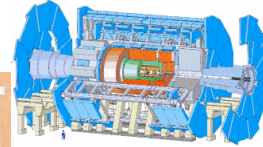
*Orsay MicroElectronic Group Associated*



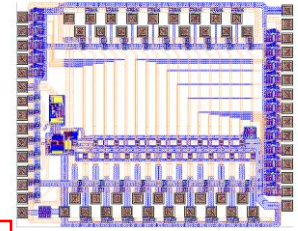
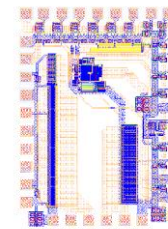
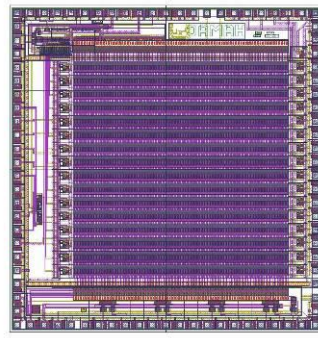
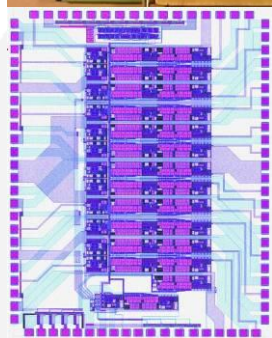
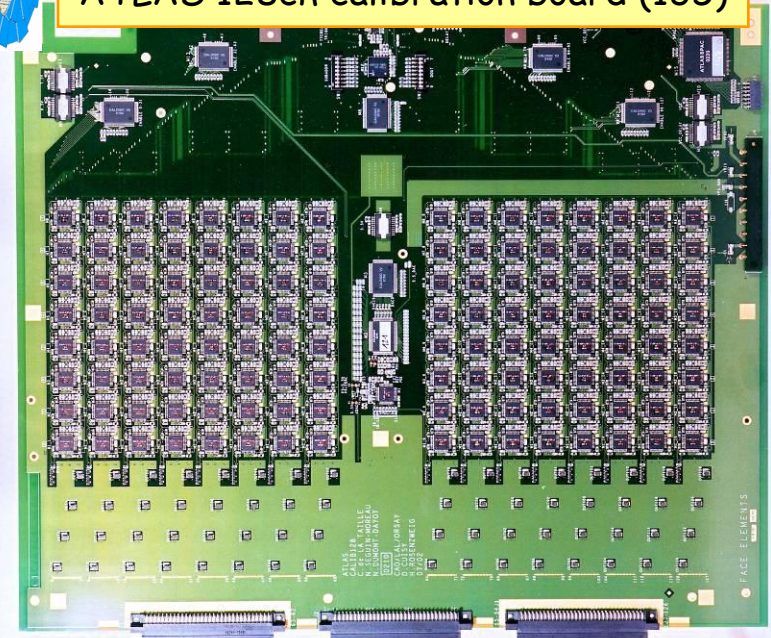
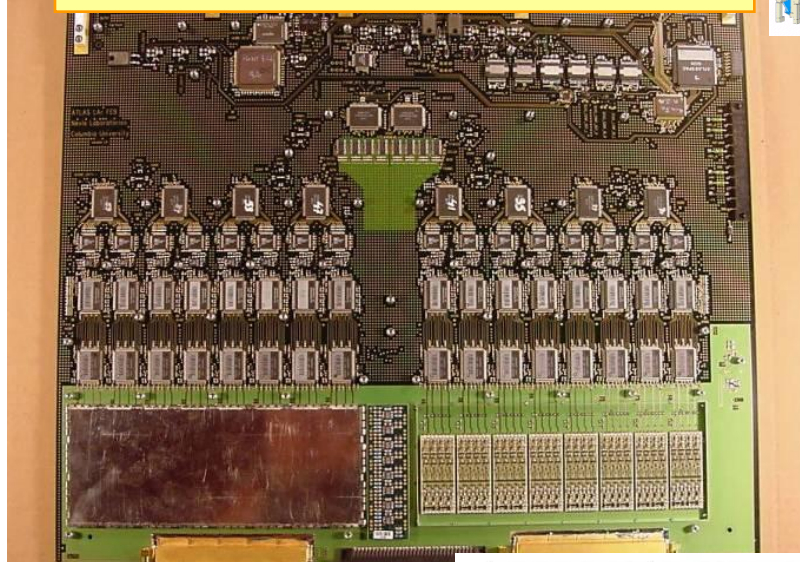




ATLAS 128ch front-end board (1700)



ATLAS 128ch calibration board (135)



**SHAPER\_V3 (1999)**  
 4 ch. tri-gain (1,10,100)  
 fast-shaper (30ns)  
 BiCMOS 1.2 $\mu$ m  
**70 000 chips**

**HAMAC (2000)**  
 16 ch 12 bits analog memory  
 Ecriture/lecture : 40/5Mhz  
 DMILL 0.8 $\mu$   
**84 000 chips**

**LOANA (2002)**  
 Low offset opamp (<10  $\mu$ V) +  
 switch HF (50 $\mu$ V  $\rightarrow$  5V à 1‰)  
 DMILL 0.8 $\mu$   
**40 000 chips**

**DAC (2003)**  
 R/2R 16 bits  
 DMILL 0.8 $\mu$   
**8 000 chips**

- Large force of microelectronics experienced engineers (~50)
- Expertise in detectors, chip design and test
- Common Cadence tools
  
- Continuous increase of chip complexity
  
- Actions :
  - Building blocks
  - Networking
  - Poles:
    - OMEGA at Orsay
    - Strasbourg
    - Dipole Lyon-Clermont

## OMEGA

is a microelectronics design center  
created in October 2007

The pole is hosted by LAL  
and gathers 4 laboratories:

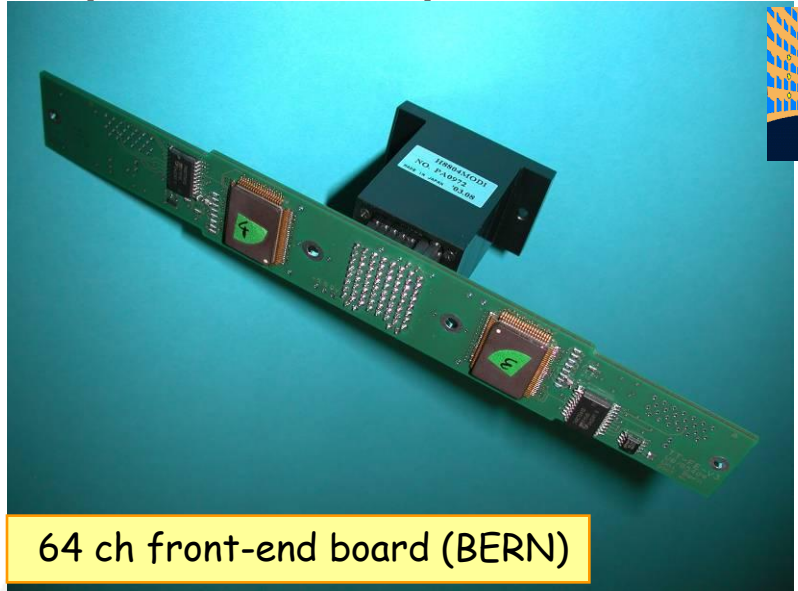
**LAL, IPNO, LLR and CSNSM**



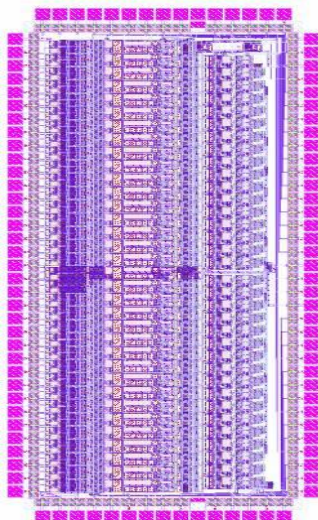
# ASIC production for OPERA target tracker



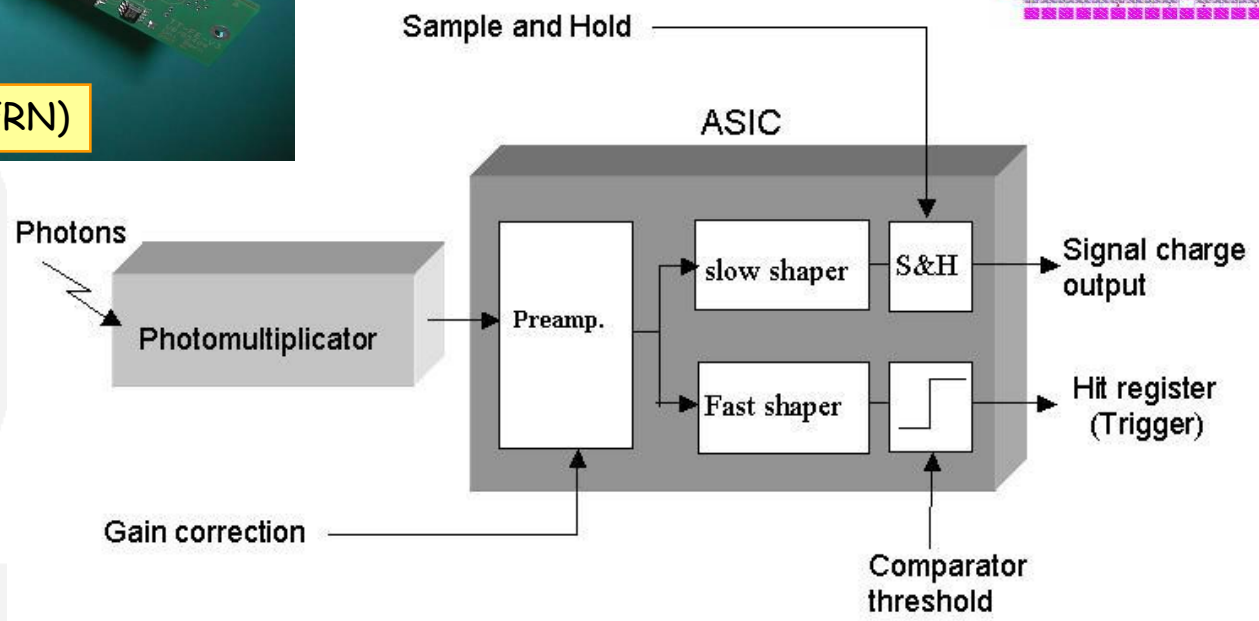
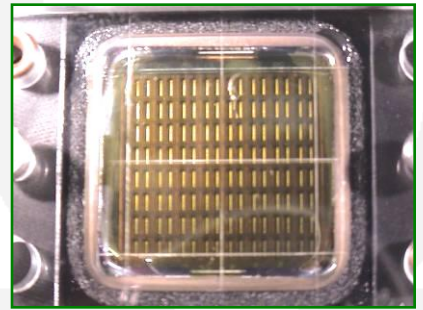
- Readout ASIC for multi-anode Photomultiplier (Hamamatsu)



**OPERA\_ROC (2002)**  
32 channels  
Variable gain preamp  
Autotrigger on 1/4 p.e.  
BiCMOS 0.8μ  
**3 000 chips**

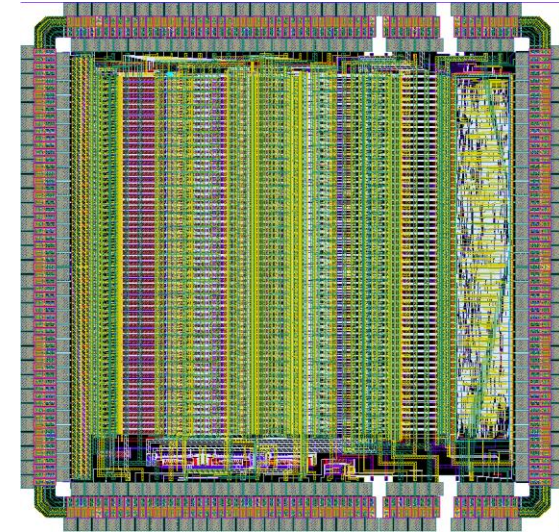
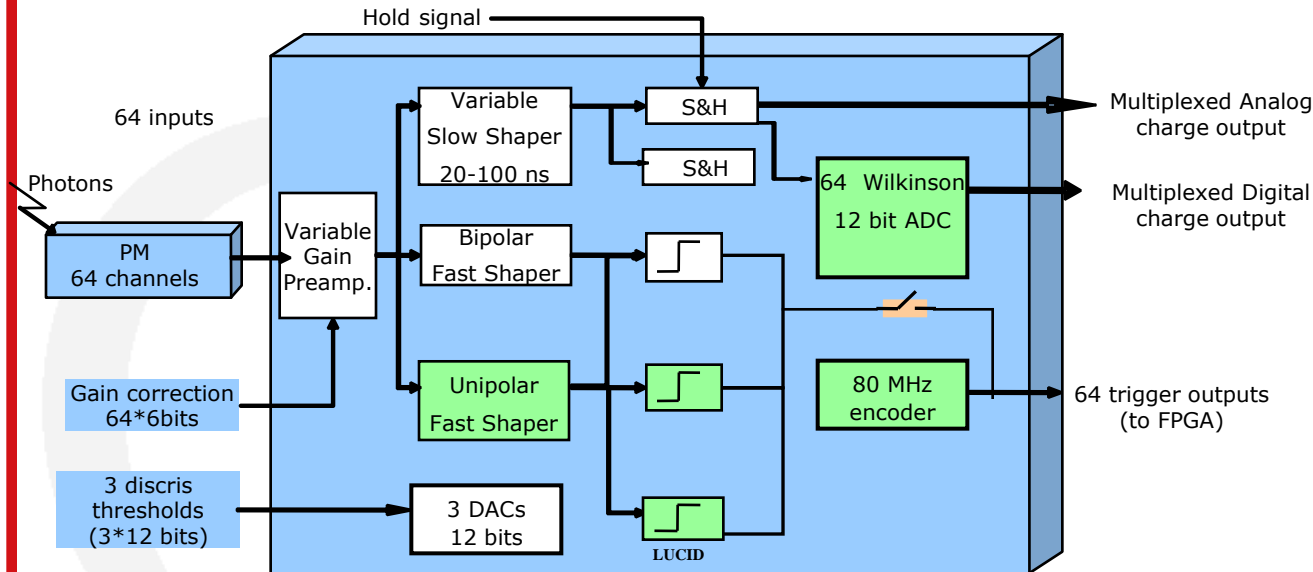


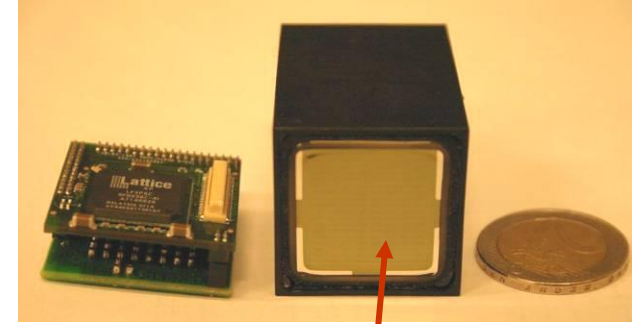
64 ch front-end board (BERN)



## Complete front-end chip for 64 channels multi-anode photomultipliers

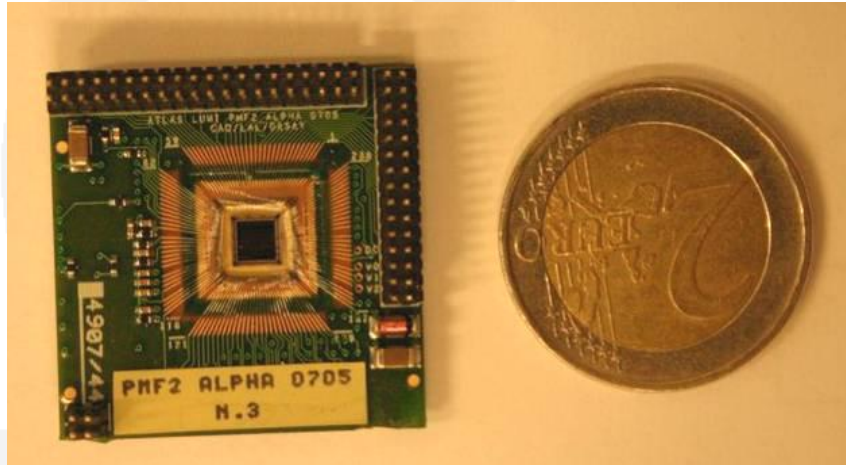
- Auto-trigger on 1/3 p.e. at 10 MHz, 12 bit charge output
- SiGe 0.35  $\mu\text{m}$ , 12 mm<sup>2</sup>, Pd = 350mW



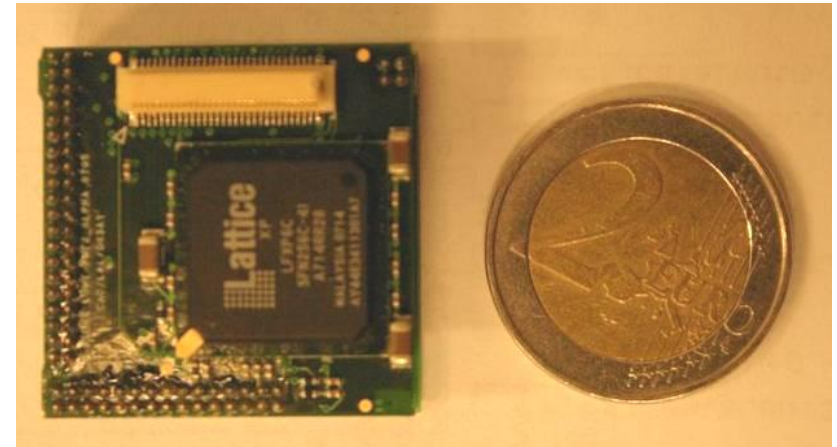


64 ch PMT

MAROC2 chip bounded at CERN



MAROC side

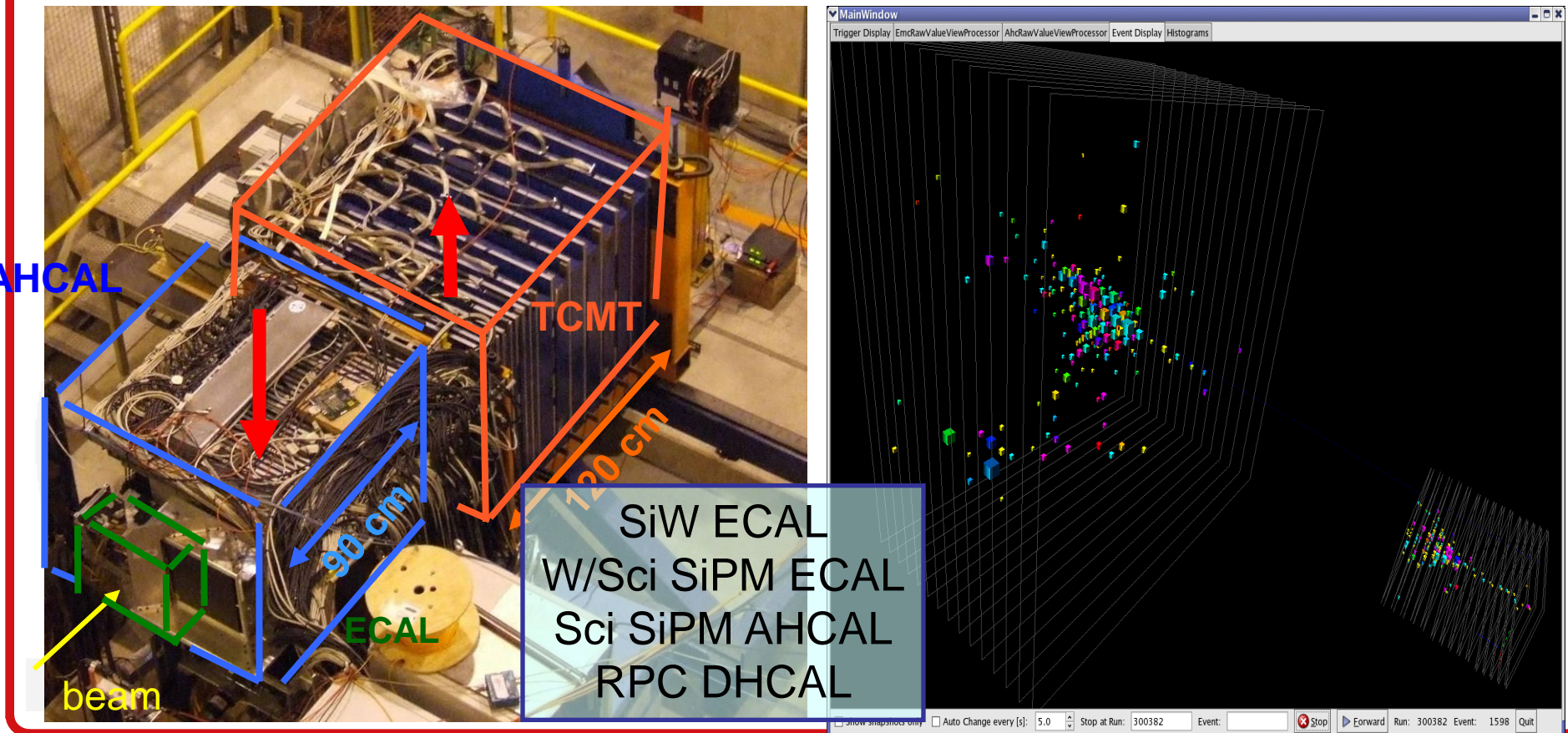


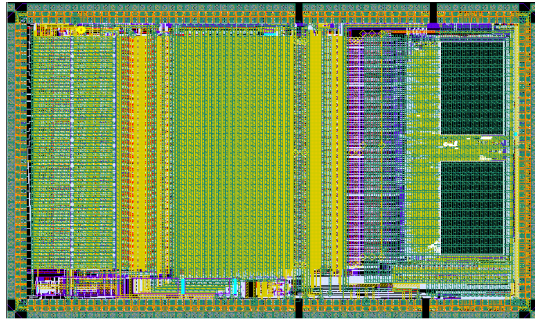
Lattice side



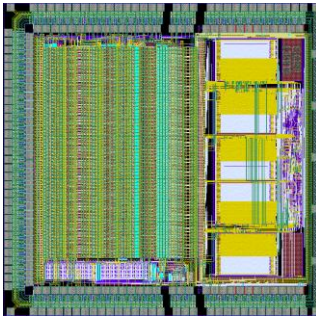
- After LHC : New imaging calorimetry...at the ILC
- Improve jets measurement by Particle flow algorithm
- CALICE : 281 phys., 47 labs, 12 countries.

Chairperson : JC Brient <http://llr.in2p3.fr/activites/physique/flc/calice.htm>

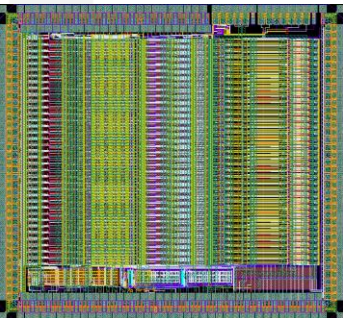




**SPIROC**  
Analog HCAL  
(SiPM)  
36 ch. 32mm<sup>2</sup>  
June 07

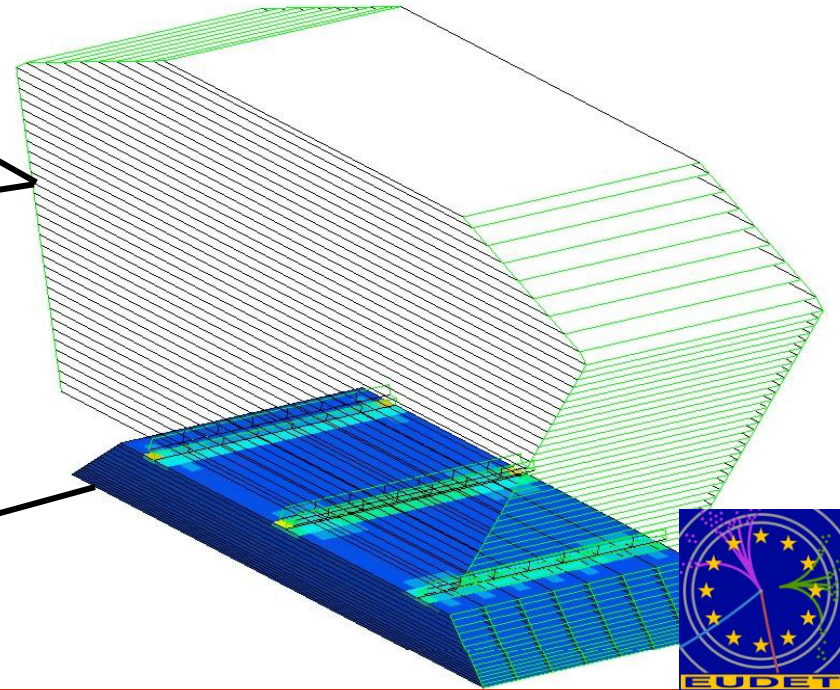


**HARDROC**  
Digital HCAL  
(RPC,  $\mu$ megas or GEMs)  
64 ch. 16mm<sup>2</sup>  
Sept 06



**SKIROC**  
ECAL  
(Si PIN diode)  
36 ch. 20mm<sup>2</sup>  
Nov 06

- Technological prototypes : full scale modules ( $\sim 2\text{m}$ )
- EUDET EU funding (06-09)
- ECAL, AHCAL, DHCAL
- B=5T

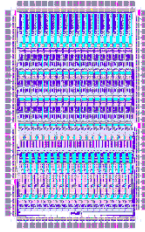
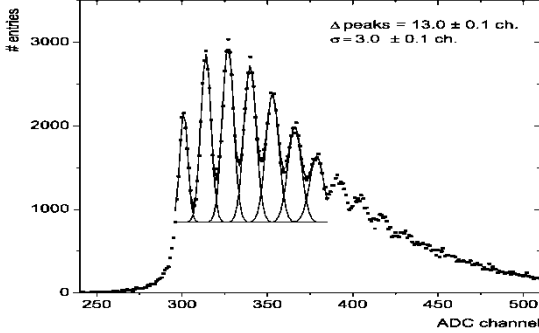




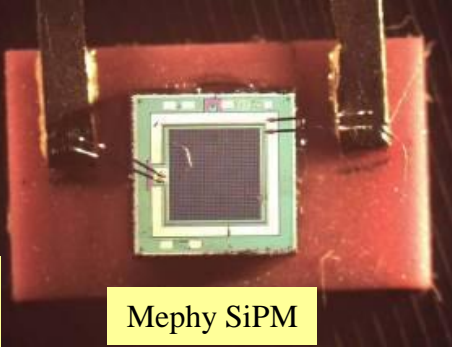
# CALICE AHCAL testbeam prototype



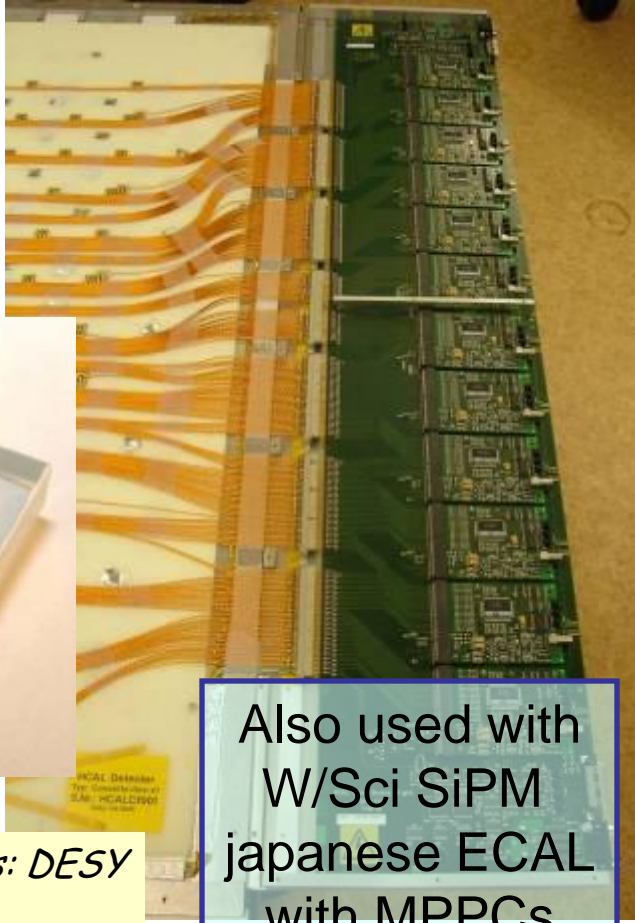
- Hadronic calorimeter prototype for the ILC : 1 cubic metre, 38 layers, 2cm steel plates
- **8000 tiles with SiPMs** fabricated by MePHY group



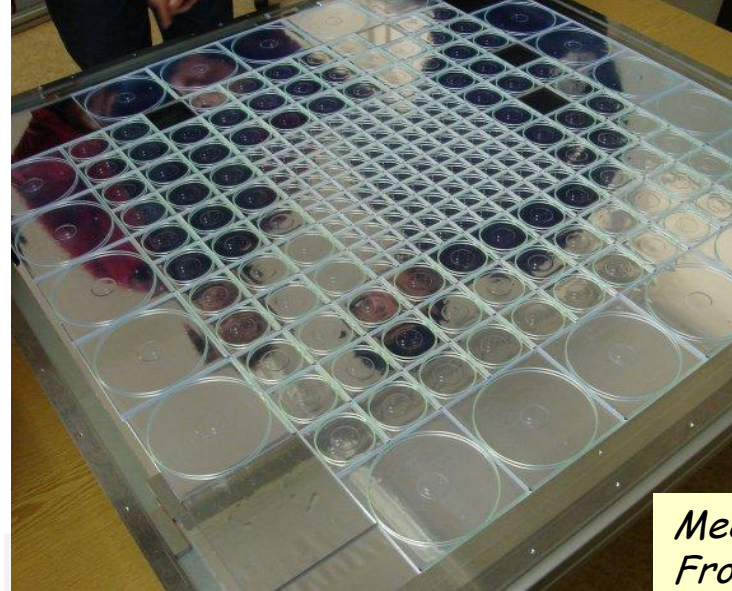
FLC SiPM ASIC



Mephy SiPM

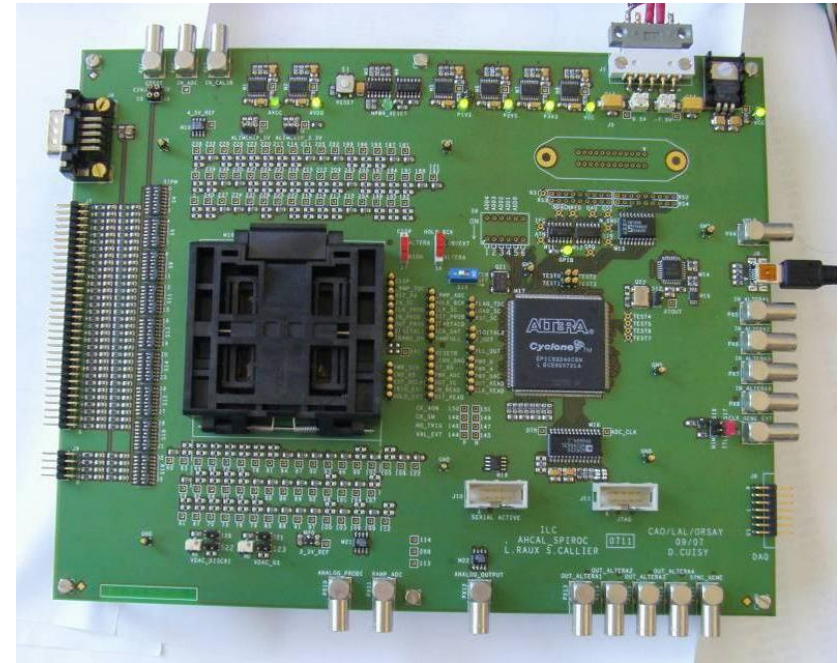
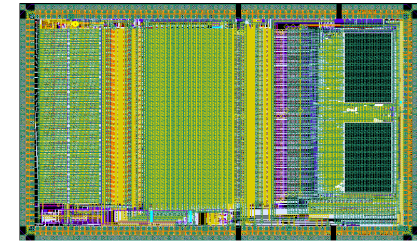


Also used with W/Sci SiPM japanese ECAL with MPPCs



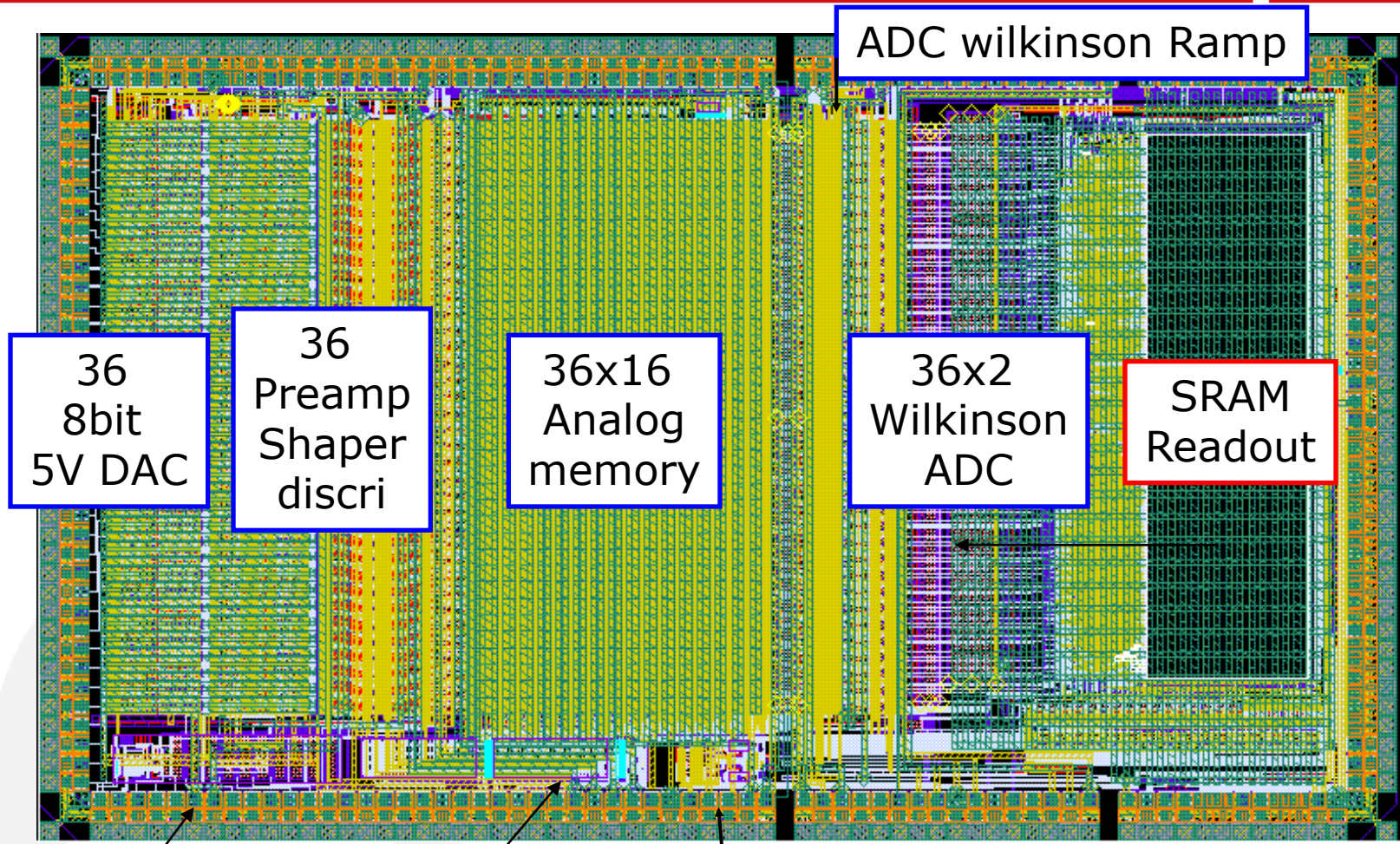
Mechanics and front end boards: DESY  
Front end ASICs: LAL

- SPIROC : Silicon Photomul. Integrated Readout Chip
  - 36 channels
  - Charge measurement
  - Time measurement
  - Autotrigger on MIP or spe
  - Sparsified readout compatible with EUDET 2<sup>nd</sup> generation DAQ
  - Chips daisy-chained
  - Pulsed power -> 25  $\mu$ W/ch
- Fabricated in SiGe AMS 0.35  $\mu$ m
  - Submitted in june 07
  - Chip area : 30 mm<sup>2</sup>





# SPIROC layout

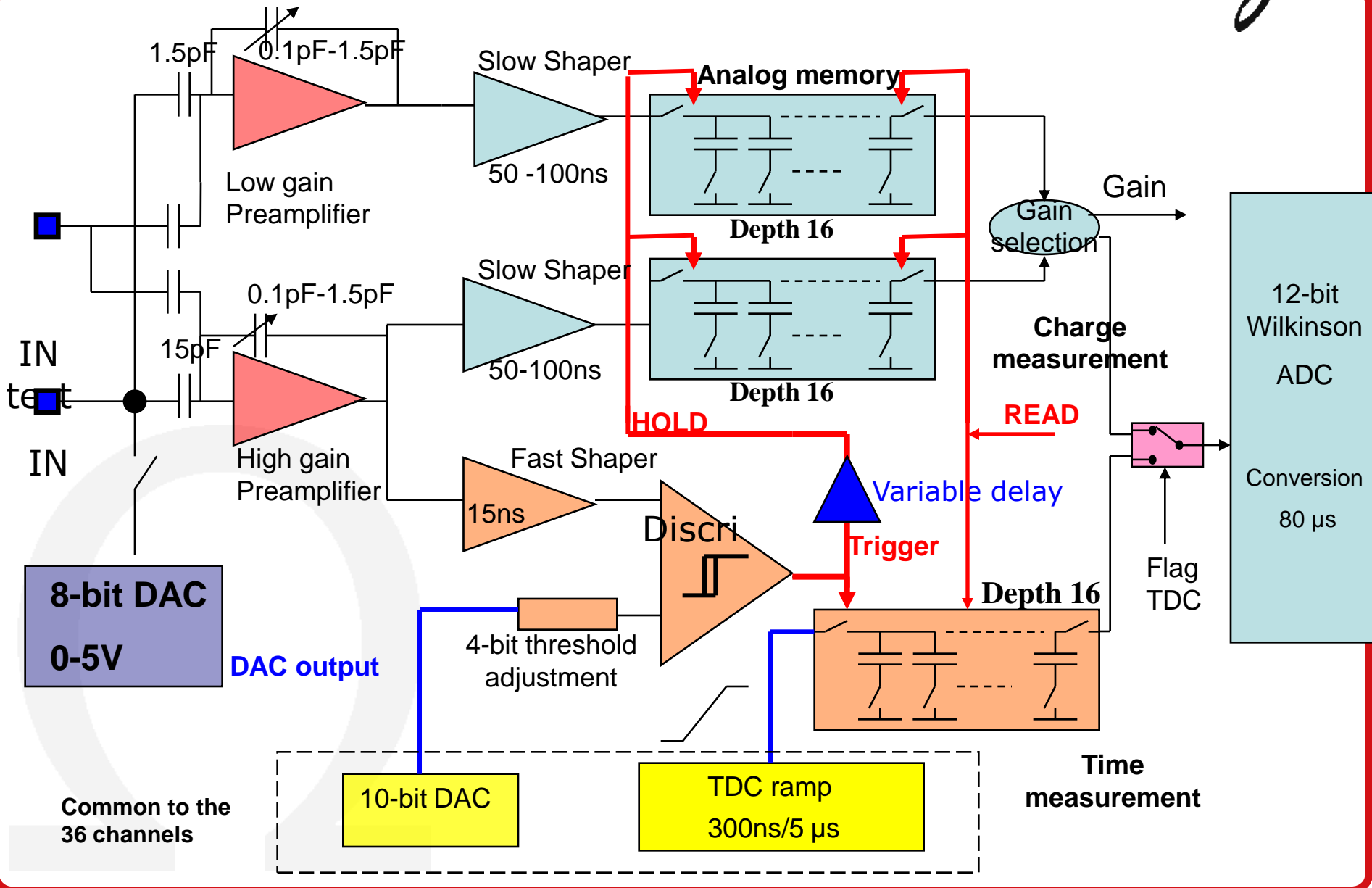


**Fabricated in SiGe AMS 0.35  $\mu\text{m}$   
Submitted in june 2007  
Chip area : 30 mm<sup>2</sup> (4.2mm x 7.2mm)**



# SPIROC : One channel schematic

*Omega*

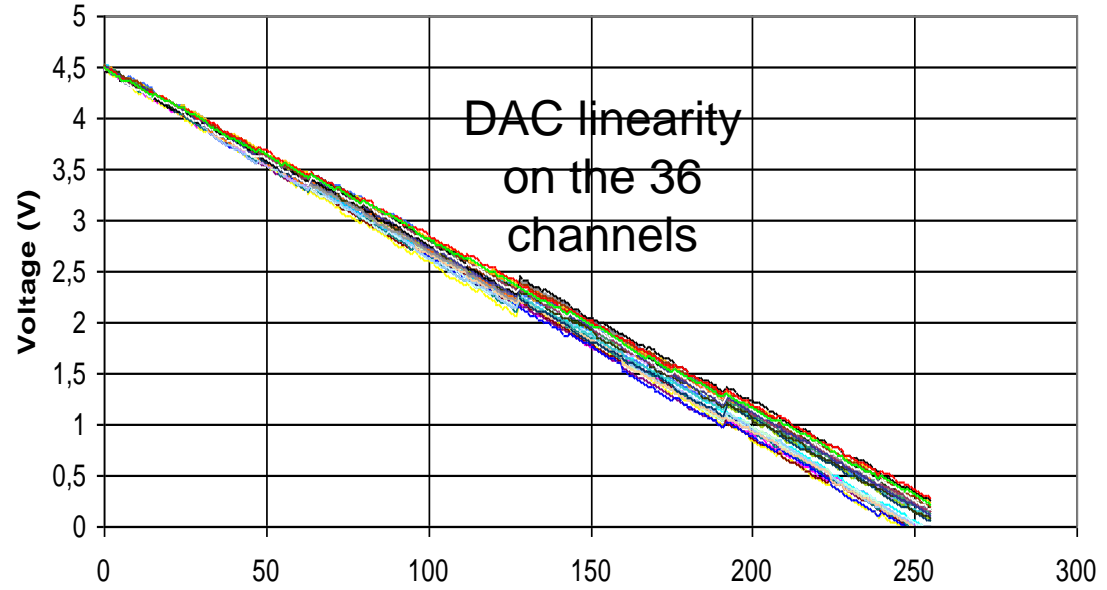




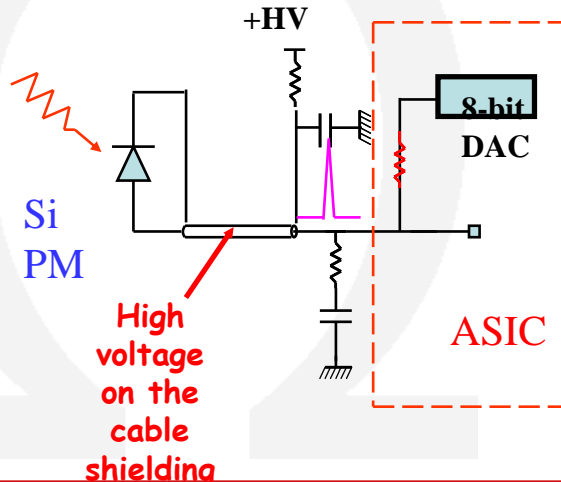
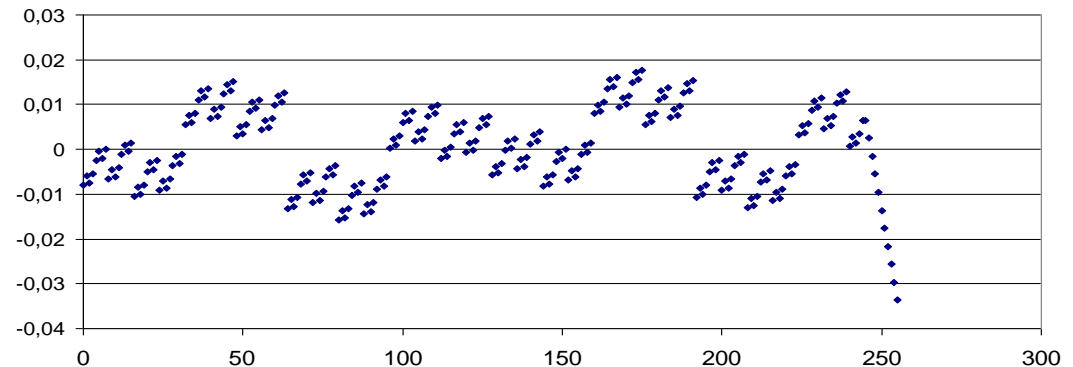
# Input DAC

- **Input DAC to optimize SiPM bias voltage**
- **8-bit DAC, 5V range**
- **LSB=20mV**
- **36 DAC : one per channel**
- **Ultra low power (1 $\mu$ W) : no power pulsing**
- **Can sink 10  $\mu$ A leakage current**
- **Linearity :  $\pm$  2%**
- **DAC uniformity between the 36 channels :  $\sim$ 3%**

DAC linearity



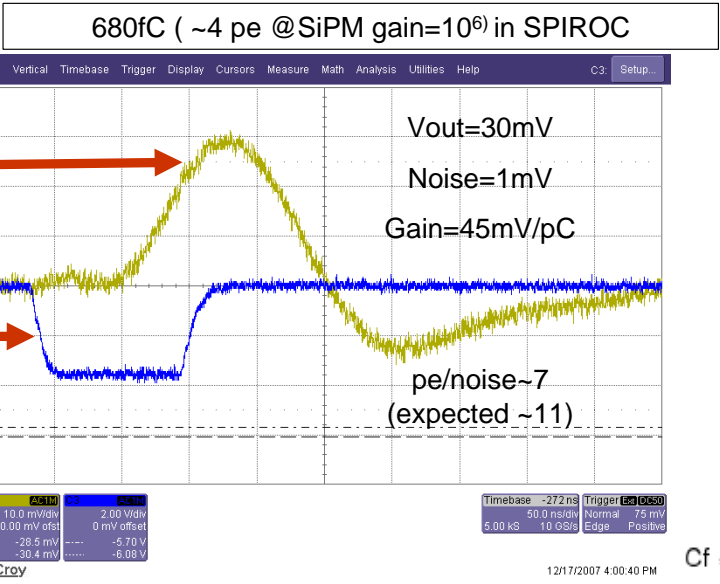
DAC



# Charge measurement



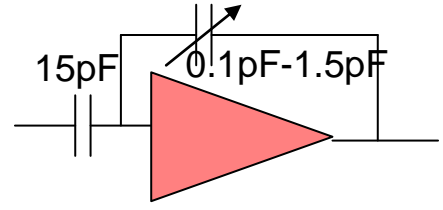
High gain channel output



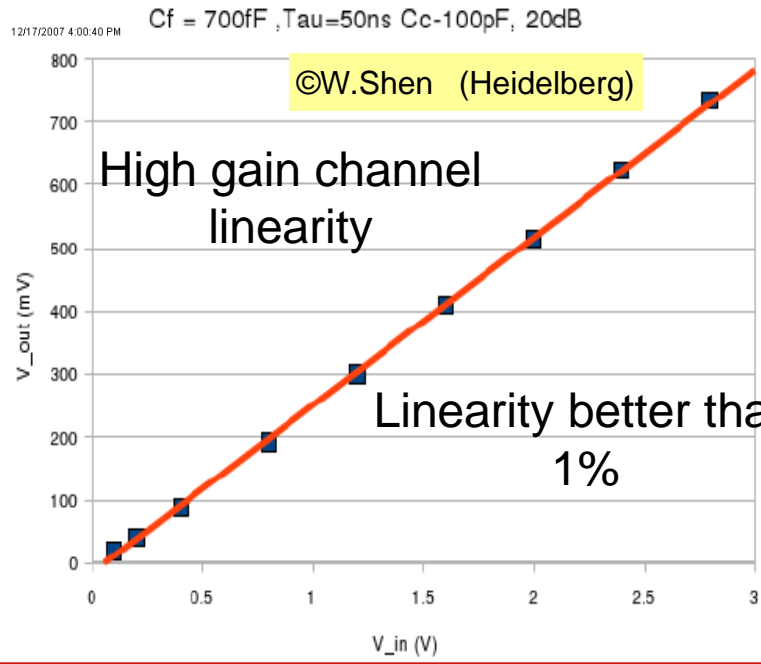
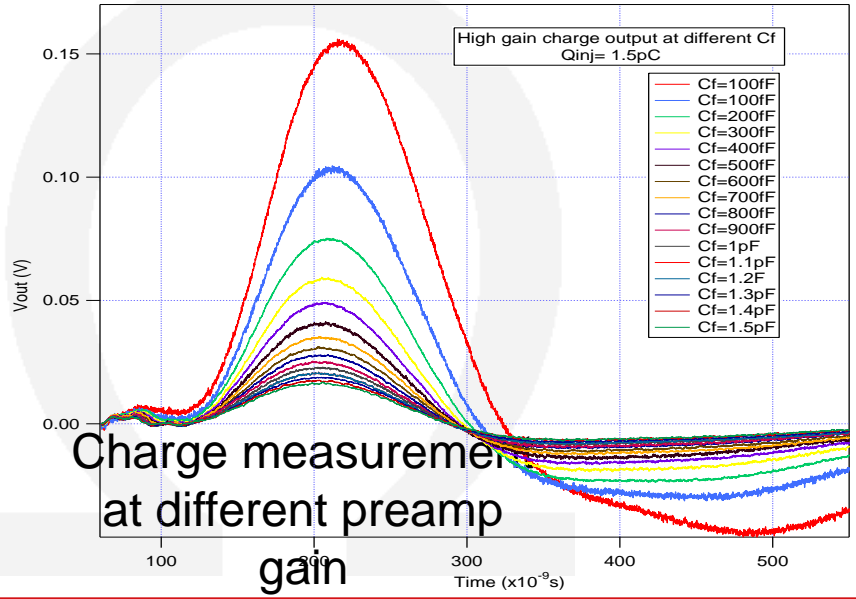
Charge measurement

Auto trigger

Set up:  
Cf=400fF  
Tau=50ns



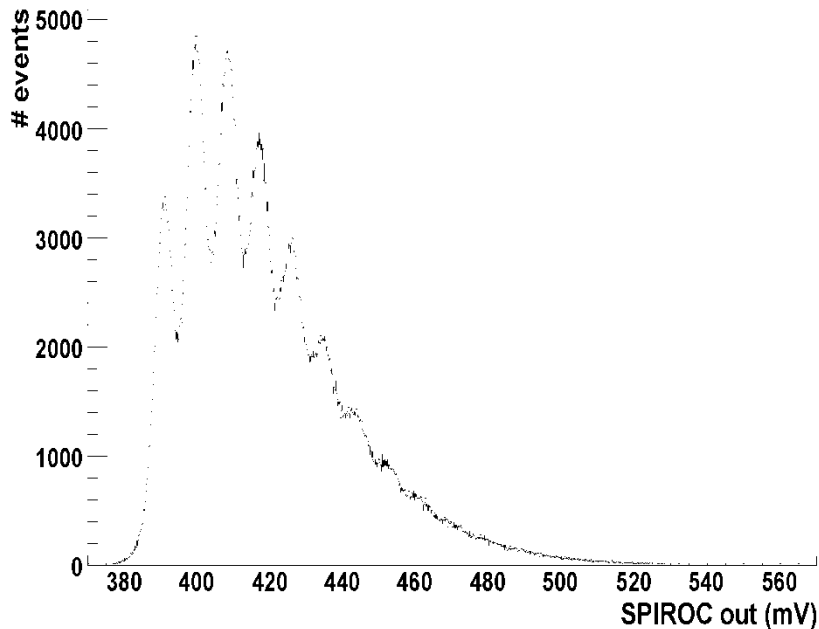
Low noise charge preamplifier  
capacitively coupled = **voltage preamplifier**  
Preamp noise : 1.4 nV/sqrt(Hz)



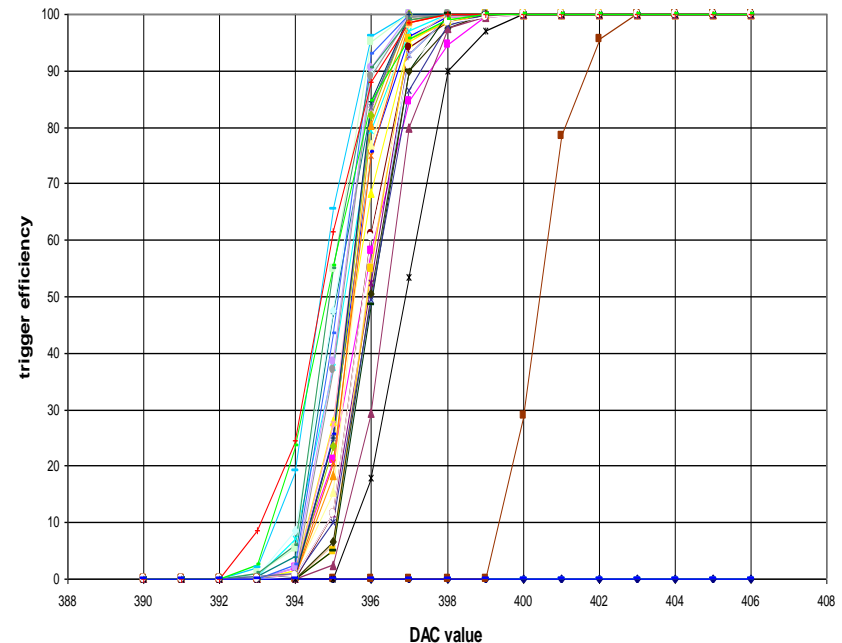


- Good analog performance
  - Single photo-electron/noise = 8
  - Auto-trigger with good uniformity
  - Complex chip : many more measurements needed

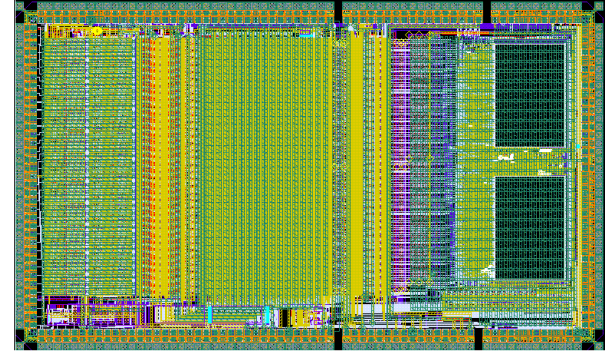
SiPM 753 SPIROC HG 100fF 50ns external hold



S-curves



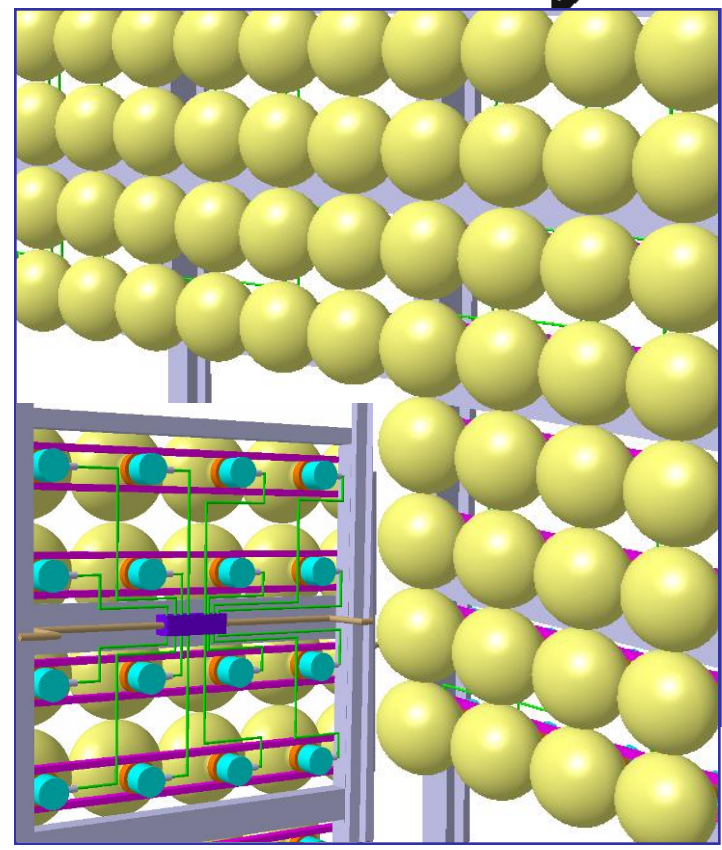
- Internal input 8-bit DAC (0-5V) for individual SiPM gain adjustment
- **Energy measurement : 14 bits**
  - 2 gains (1-10) + 12 bit ADC 1 pe  $\rightarrow$  2000 pe
  - Variable shaping time from 50ns to 100ns
  - pe/noise ratio : 11
- **Auto-trigger on 1/3 pe (50fC)**
  - pe/noise ratio on trigger channel : 24
  - Fast shaper :  $\sim$ 10ns
  - Auto-Trigger on  $\frac{1}{2}$  pe
- Time measurement :
  - 12-bit Bunch Crossing ID
  - 12 bit TDC step  $\sim$ 100 ps
- Analog memory for time and charge measurement : depth = 16
- Low consumption :  $\sim$ 25 $\mu$ W per channel (in power pulsing mode)
- Individually addressable calibration injection capacitance
- Embedded bandgap for voltage references
- Embedded 10 bit DAC for trigger threshold and gain selection
- Multiplexed analog output for physics prototype DAQ
- 4k internal memory and Daisy chain readout



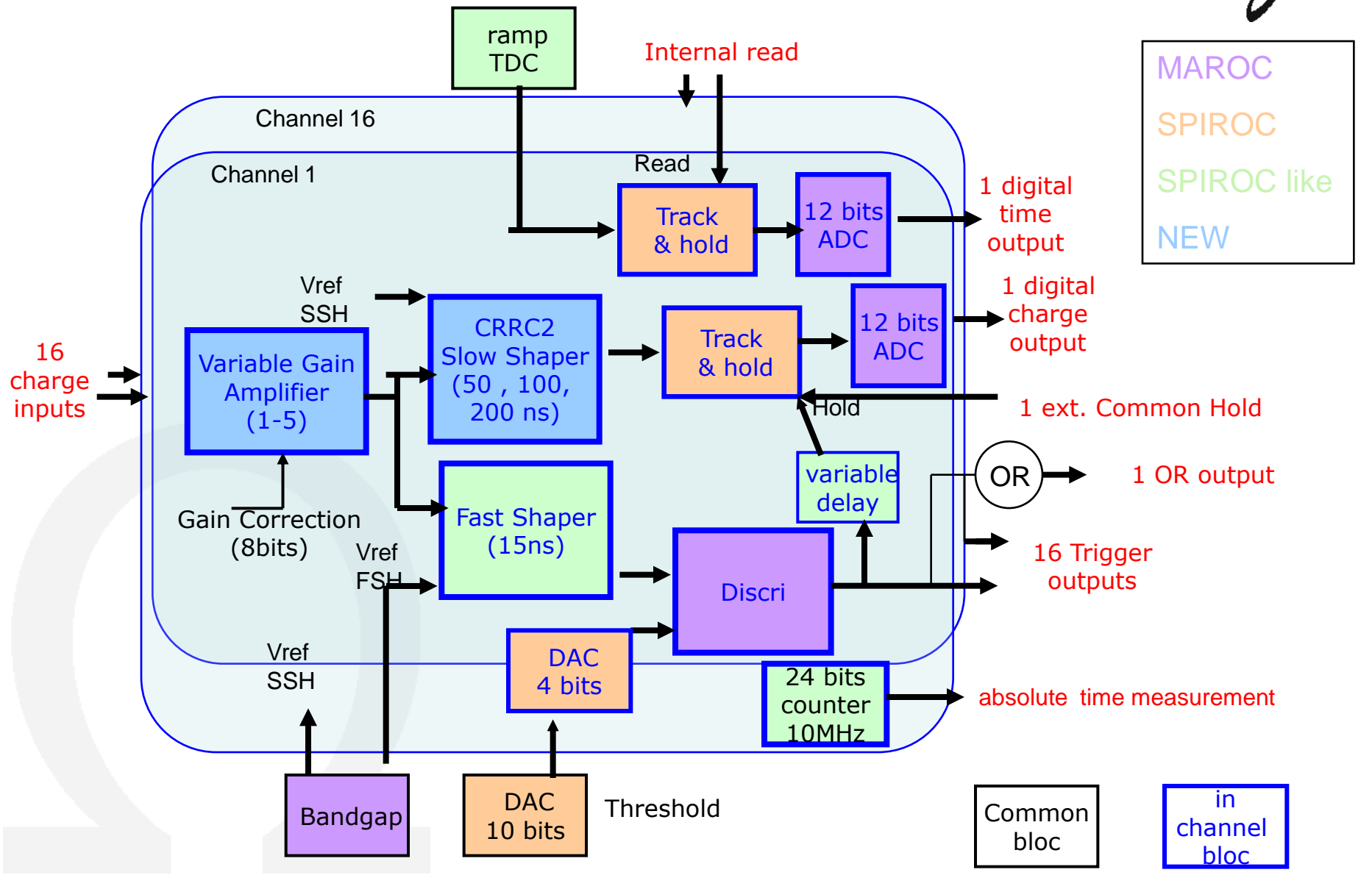


## PMm<sup>2</sup> : large photodection area

- **“PMm2” (2006 – 2009), funded by the ANR** : LAL, IPNO, LAPP, Photonis
- Replace large PMTs (20”) by groups of smaller ones (12”)
  - central 16ch ASIC (**PaRISROC**)
  - 12 bit charge + 12 bit time
  - water-tight, common High Voltage
  - Only one wire out (DATA + VCC)
  - **Target low cost**
  - Reuse many parts from MAROC & SPIROC
- Application : large water Cerenkov neutrino
  - 1ns time resolution
  - High granularity
  - scalability

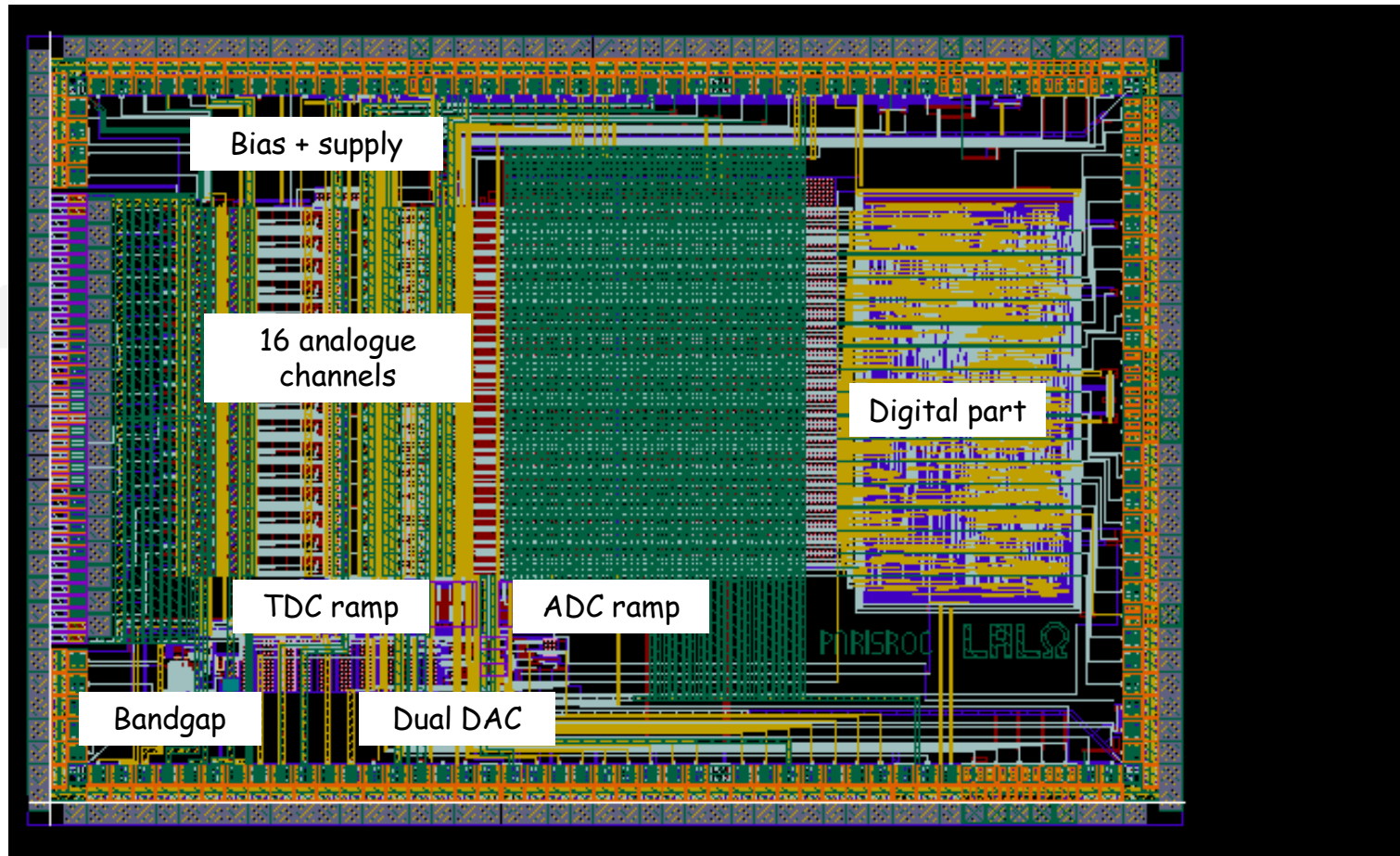


# PMm<sup>2</sup> ASIC Architecture (Analog part)

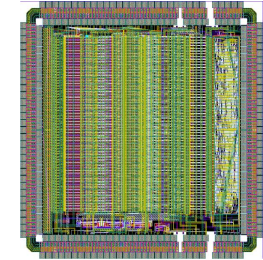




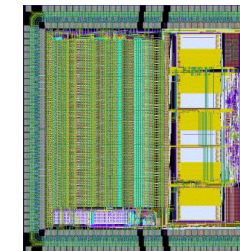
- 16 channels read out chip for Photomultiplier array
- SiGe 0.35  $\mu\text{m}$  technology. Chip submitted jun 08



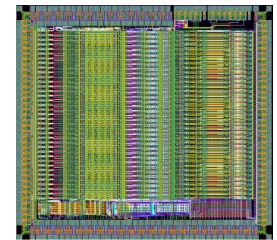
- A strong team of 10 ASIC designers...
  - around 20% of IN2P3 designers
  - A team with critical mass : pole created in 2007 = OMEGA
  - Expertise in low noise, low power high level of integration ASICs
  - 2 designers/ project
  - 2 projects/designer
  - Regular design meetings
- Within the LAL Electr. Depart. (50 p.)  
(Support for tests, measurements, PCBs...)
- Collaboration with IPNO, LLR, CSNSM
- A steady production
  - A strong on-going R&D
  - Building blocks SiGe 0.35 $\mu$ m



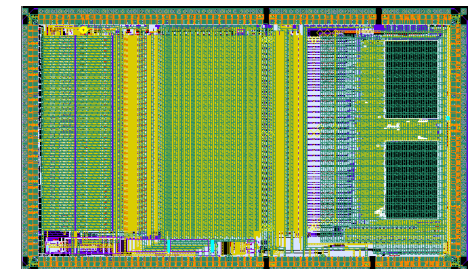
**MAROC 2**



**HARDROC**



**SKIROC**



**SPIROC**



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- OMEGA Web Site:

<http://omega.in2p3.fr>

- Contact:

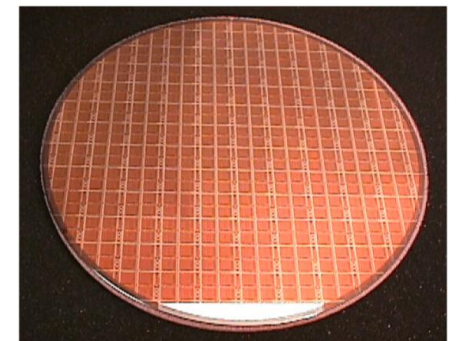
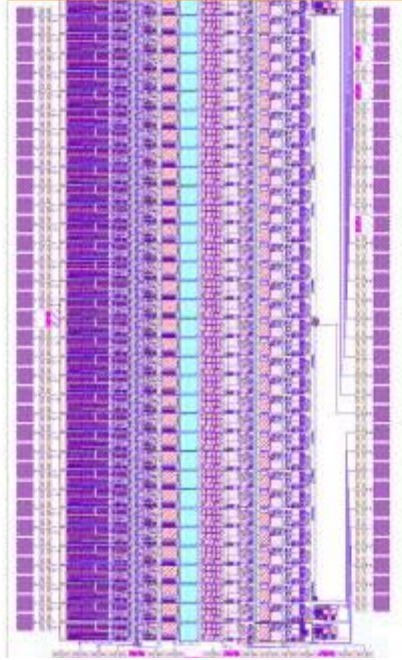
Christophe de La Taille: [taille@lal.in2p3.fr](mailto:taille@lal.in2p3.fr)



## (R)evolution of analog electronics

- ASICs : Application Specific Integrated Circuits
  - Access to foundries through **multiproject runs** (MPW)
  - Reduced development costs : 600-2000 €/mm<sup>2</sup> compared to dedicated runs (100-2000 k€)
  - **Full custom layout, at transistor level**
  - mostly **CMOS & BiCMOS**
- Very widespread in high Energy Physics
  - High level of integration, limited essentially by power dissipation and parasitic couplings (EMC)
  - Better **performance** : reduction of parasitics
  - Better **reliability** (less connections)
  - But **longer developpement time**

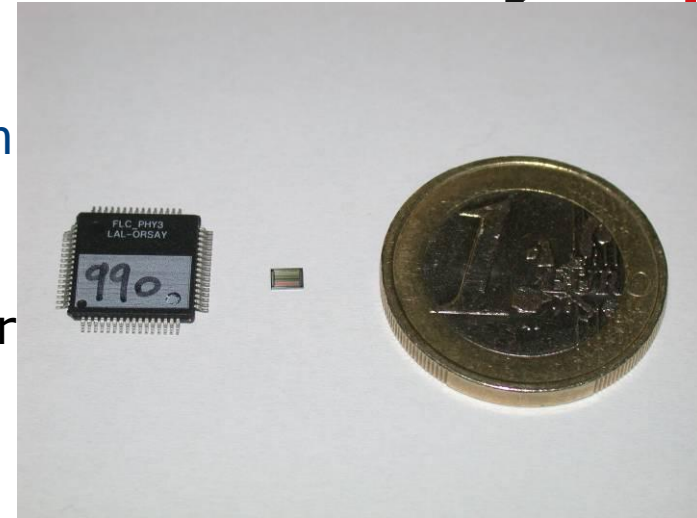
Layout 32ch ASIC



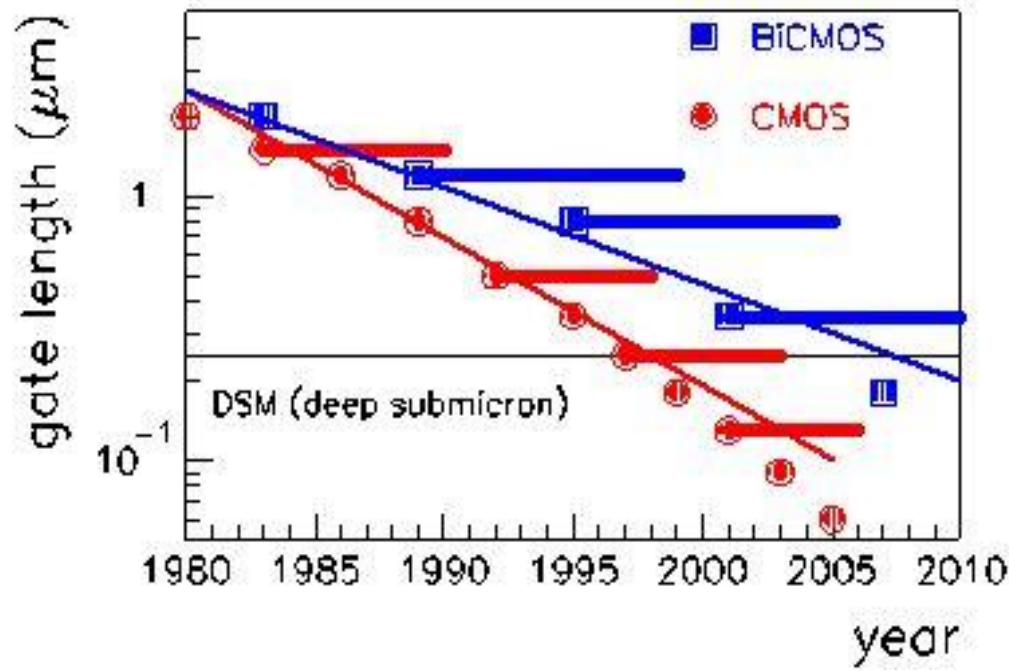
300 mm wafer (IBM)



- MPW (multi-project wafers)
  - CMOS 0.35 $\mu$ m (AMS) : 650 €/mm<sup>2</sup>
  - BiCMOS SiGe 0.35  $\mu$ m (AMS) : 900 €/mm<sup>2</sup>
  - CMOS 0.13 $\mu$ m (STm) : 2500 €/mm<sup>2</sup>
  - CMOS 90 nm (STm) : 5000 €/mm<sup>2</sup>
  - Usually a few 10 to 100 pieces in a MPW run
- Production runs
  - Masks : 91 k€ (CMOS 0.35 $\mu$ m)
  - 8" wafers : 4 k€, useful area : 25 000 mm<sup>2</sup> = several thousands of chips
- Packaging
  - Ceramic : 20-30€/chip
  - Plastic : 2k€ + 1-2 €/chip
- Example : chip 10mm<sup>2</sup> 16 channels
  - 100 chips (MPW) : 120€/chip, 7€/channel
  - 10 000 chips (4wafers) : 12€/chip < 1€/channel



- Differences between analog/mixed signal and digital technologies
  - **Very fast** evolution of **digital technologies** (faster design migration)
  - More « perene » analog technologies (SiGe, BiCMOS...) (driven by mobile telecom and automotive)



## low voltage

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